2305L

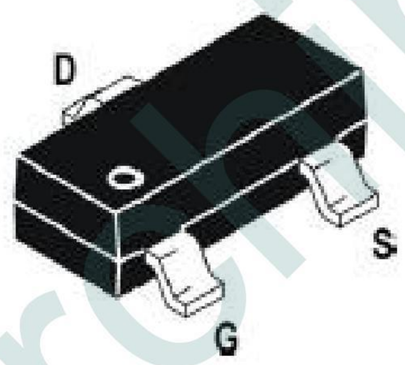
P-Channel Trench Power MOSFET

- VDS=-16V, ID=-5.8A
- RDS(ON) =22mΩ @ VGS = -4.5V
- RDS(ON) =29mΩ @ VGS = -2.5V
- High Power and Current Handing Capability
- Lead Free Product is Acquired
- Surface Mount Package

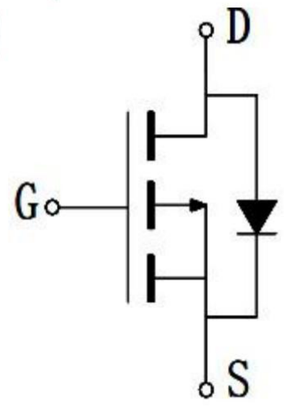
Application

- PWM Applications
- Load Switch
- Power Management

Package



SOT23-3



Schematic Diagram

Absolute Maximum Ratings (Tc=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-16	V
V_{GSS}	Gate-Source Voltage		±12	V
I_D	Continuous Drain Current	T_C = 25℃	-5.8	A
		T_C = 100℃	-3.5	
I_{DM}	Pulsed Drain Current		-20	
P_D	Power Dissipation	T_C = 25℃	1.5	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		83.3	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

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